

# ISC022N10NM6ATMA1

Data Sheet

Manufacturers	Infineon Technologies Corporation	
Package/Case	PG-TSON-8	
Product Type		and the second sec
RoHS		1. 55D
Lifecycle		
		Images are for reference only
Please submit RFQ for ISC022N10NM6ATMA1 or Email to us: sales@oyaga.com We will contact you in 12 hours.		

# **General Description**

ISC022N10NM6 OptiMOS<sup>TM</sup> 6 100 V in normal level is setting the new technology standard in the field of discrete power MOSFETs. Compared to alternative products, Infineon's leading thin wafer technology is enabling significant performance benefits.

Infineon's OptiMOS<sup>TM</sup> 6 industrial power MOSFET 100 V is designed for high switching frequency application such as telecom and server power supply, but also the ideal choice for other applications such as solar, power tools and drones.

In the SuperSO8 package it achieves ~20% improvements in on-state resistance ( $R_{DS(on)}$ ) and 30% better figure of merits (FOM -  $R_{DS(on)} \times Q_g$ and  $Q_{gd}$ ) compared to the previous technology OptiMOS<sup>TM</sup> 5. This enables designers to increase efficiency, allowing easier thermal design and less paralleling, leading to system cost reduction.

Compared to OptiMOS<sup>™</sup> 5, the new technology achieves:

~20% lower R<sub>DS(on)</sub>

30% improved  $FOM_g$  and 40% better  $FOM_{gd}$ 

Lower and softer reverse recovery charge (Q<sub>rr</sub>)

Ideal for high switching frequency

MSL 1 classified according to J-STD-020

175 °C junction temperature rating

High avalanche energy rating

Pb-free lead plating

RoHS compliant

Low conduction losses

- Low switching losses
- Fast turn on and off
- Less paralleling required
- Robust reliable performance
- Environmentally friendly
- Less paralleling required
- Telecom
- Server
- Drones
- Robotics
- Solar
- Power tools
- Battery management system

# Features

DS(on)

30% improved FOM

g

#### gd

Lower and softer reverse recovery charge (Q

rr

- Ideal for high switching frequency
- MSL 1 classified according to J-STD-020
- 175 °C junction temperature rating
- High avalanche energy rating
- Pb-free lead plating
- RoHS compliant
- Low conduction losses
- Low switching losses
- Fast turn on and off
- Less paralleling required
- Robust reliable performance
- Environmentally friendly
- Less paralleling required

## **Related Products**



#### ISC027N10NM6ATMA1

Infineon Technologies Corporation PG-TDSON-8



# ISZ0703NLSATMA1

Infineon Technologies Corporation PG-TSDSON-8





# Application

Telecom

Drones

Server

Robotics

Solar

Power tools

Battery management system



ISC058N04NM5

ISC011N06LM5ATMA1

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## ISP12DP06NM

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### ISC012N04LM6

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# ISC017N04NM5ATMA1

Infineon Technologies Corporation PG-TDSON-8